V_{DSS}	-100 V
I_D	-3 A
$R_{DS(ON)}$	282 mΩ

FEATURES

The 3P10 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 5V. This device is suitable for use as a Battery protection or in other Switching application.

3P10

FEATURES

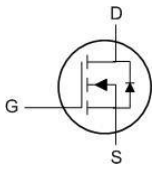
V_{DS} = -100V I_D =-3A

$R_{DS(ON)}$ < 300mΩ @ V_{GS}=-10V



SOT23-3L top view

Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25°C	Continuous Drain Current, V_{GS} @ -10V[1]	-3	A
I_D@T_A=70°C	Continuous Drain Current, V_{GS} @ -10V[1]	-1.7	A
I_{DM}	Pulsed Drain Current[2]	-9	A
P_D@T_A=25°C	Total Power Dissipation[3]	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	125	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	80	°C/W

Electrical characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-100	---	---	V
△BVDSS/△TJ	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.0624	---	V/℃
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-3A	---	282	300	mΩ
		V_{GS}=-4.5V , I_D=-2A	---	310	333	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1	---	-2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.5	---	mV/℃
IDSS	Drain-Source Leakage Current	V_{DS}=-100V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-100V , V_{GS}=0V , T_J=100℃	---	---	100	
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-0.8A	---	3	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	16	32	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-15V , V_{GS}=-4.5V , I_D=-0.5A	---	4.5	---	nC
Qgs	Gate-Source Charge		---	1.14	---	
Qgd	Gate-Drain Charge		---	1.5	---	
Td(on)	Turn-On Delay Time	V_{DD}=-50V , V_{GS}=-10V , R_G=3.3Ω I_D=-0.5A	---	17.6	---	ns
T_r	Rise Time		---	2.7	---	
Td(off)	Turn-Off Delay Time		---	4.5	---	
T_f	Fall Time		---	3	---	
Ciss	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	550	---	pF
Coss	Output Capacitance		---	56	---	
Crss	Reverse Transfer Capacitance		---	35	---	
IS	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	-3	A
ISM	Pulsed Source Current[2,4]		---	---	-9	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.3	V

Note :

1、The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The power dissipation is limited by 150℃ junction temperature

4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

RATING AND CHARACTERISTIC CURVES

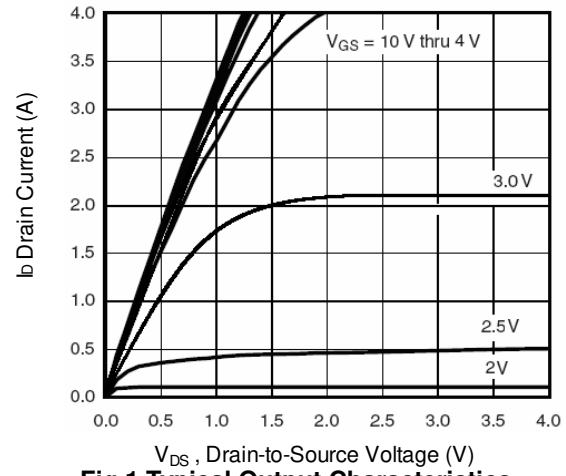


Fig.1 Typical Output Characteristics

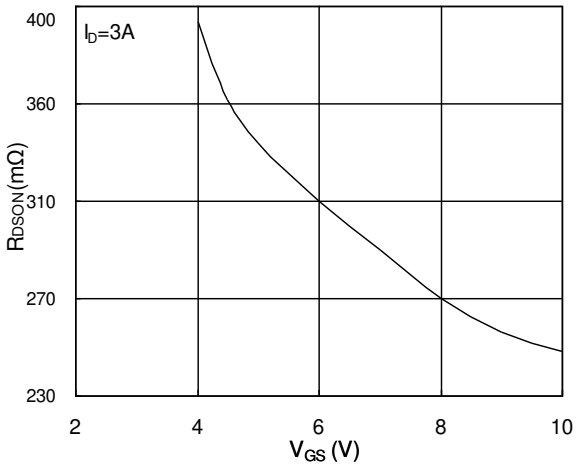


Fig.2 On-Resistance vs. Gate-Source

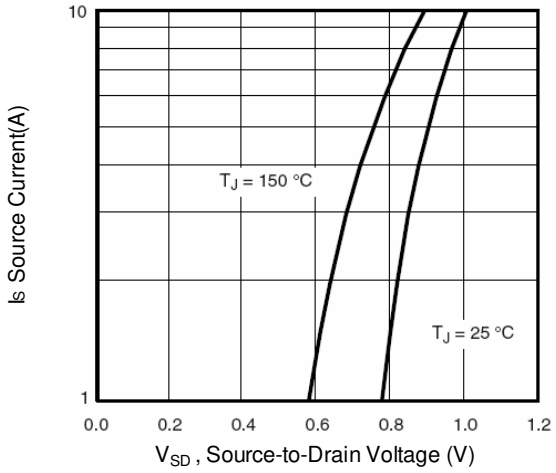


Fig.3 Forward Characteristics of Reverse

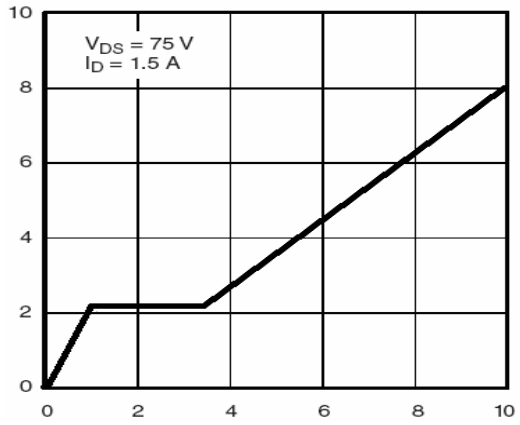


Fig.4 Gate-Charge Characteristics

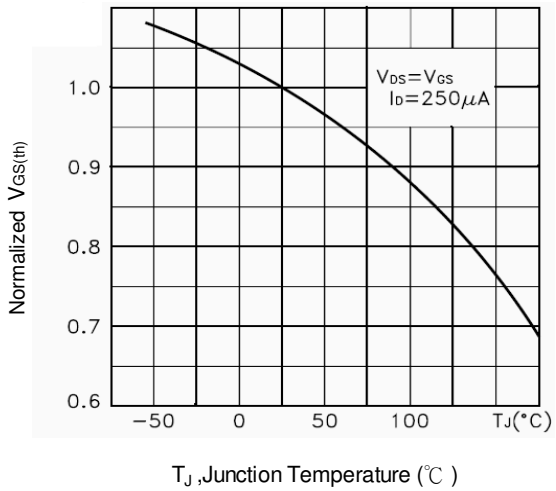


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

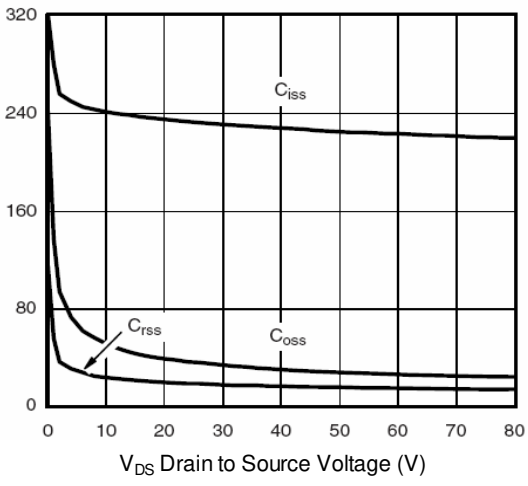


Fig.6 Capacitance

RATING AND CHARACTERISTIC CURVES

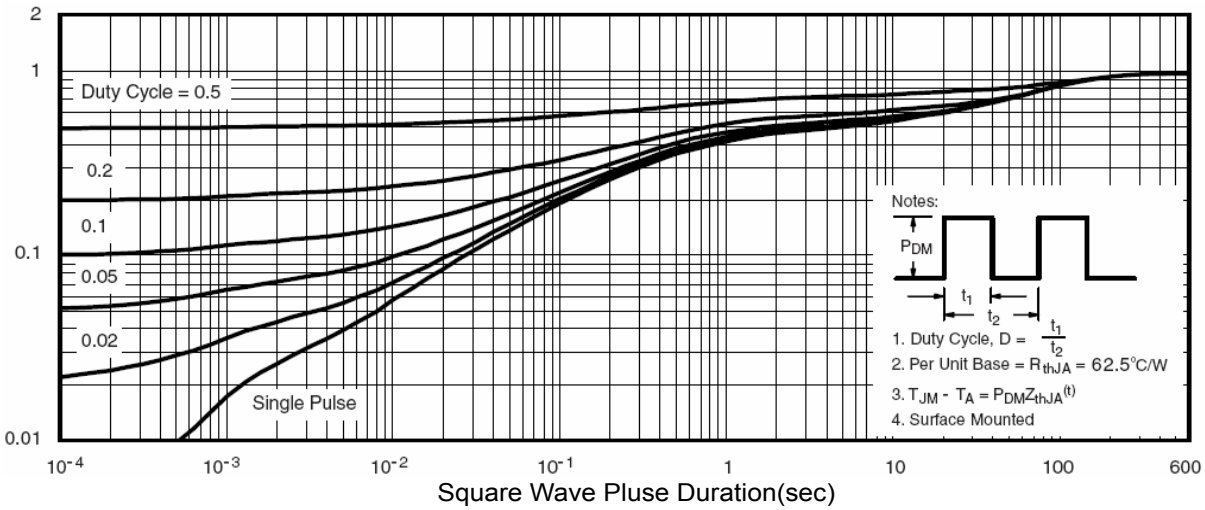


Fig.9 Normalized Maximum Transient Thermal Impedance

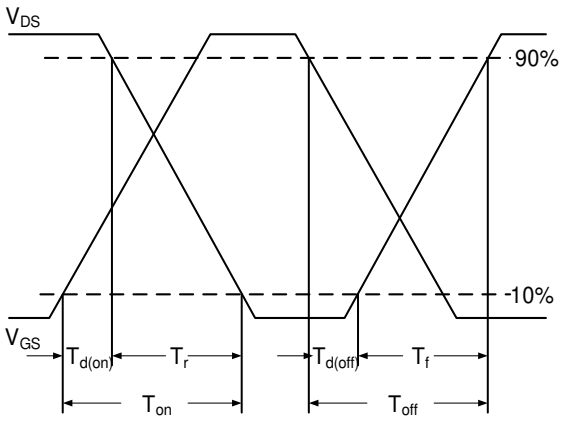


Fig.10 Switching Time Waveform

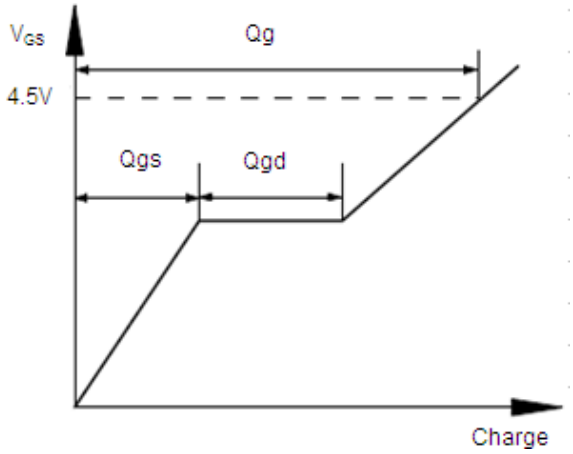
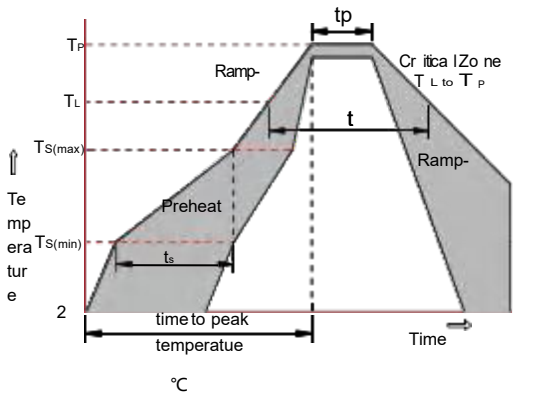


Fig.11 Gate Charge Waveform

Soldering parameters

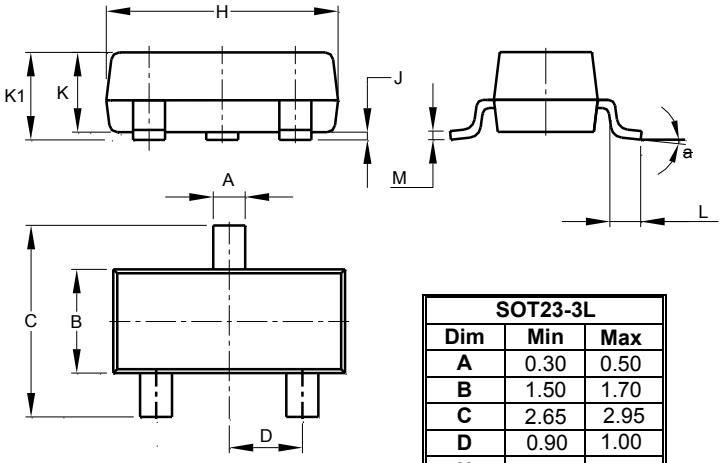
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

FIG5: Reflow condition

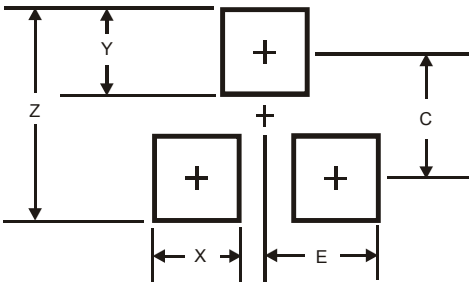


Package Dimensions & Suggested Pad Layout

SOT23-3L



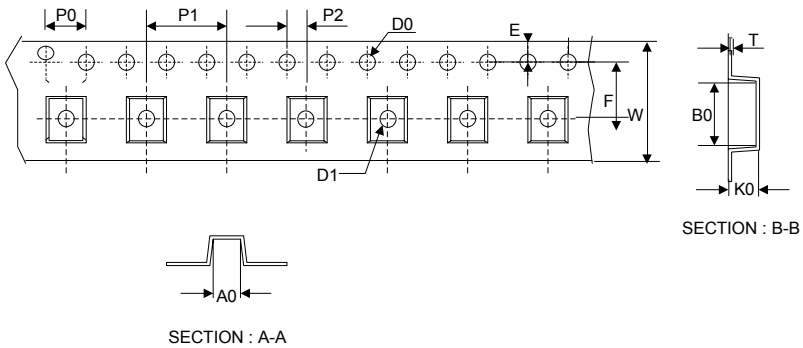
SOT23-3L		
Dim	**Min**	**Max**
A	0.30	0.50
B	1.50	1.70
C	2.65	2.95
D	0.90	1.00
H	2.82	3.02
J		0.10
K	1.05	1.15
K1	1.05	1.25
L	0.30	0.60
M	0.10	0.20
a	0°	8°
All Dimensions in mm		



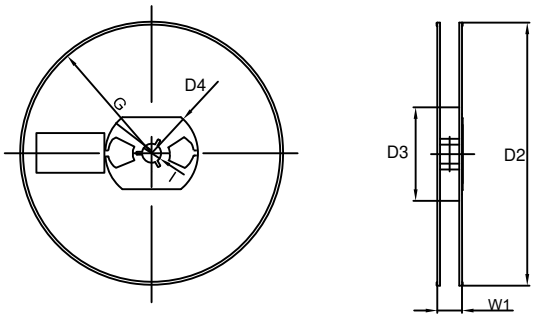
Dimensions	SOT23-3L
Z	3.3
X	0.9
Y	1.0
C	2.3
E	1.40

Tape & rell specification

Tape



7" Reel



Symbol	Dimension (mm)
P0	4.00±0.20
P1	4.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	1.05±0.20
E	1.55±0.20
F	3.60±0.20
W	8.00±0.20
A0	3.80±0.20
B0	3.50±0.20
K0	1.55±0.20
T	0.25±0.15
D2	178.0±5.0
D3	55Min.
D4	R24.0±3.0
G	R82.0±3.0
I	13.0±2.0
W1	11.0±3.0
Quantity: 3000PCS	

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